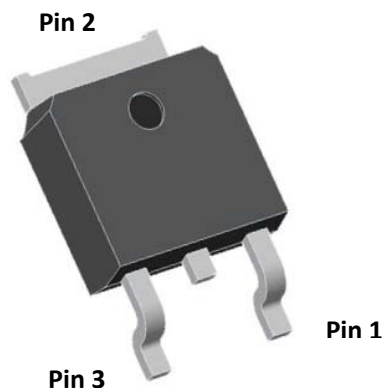


Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Part no. with suffix "Q" means AEC-Q101 qualified

Typical Applications

Typical applications are in switching power supplies, converters, automotive, freewheeling diodes, and reverse battery protection.

Mechanical Data

- **Package:** TO-252
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen free
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked

■Maximum Ratings (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR10100CDQ
Device marking code	-	-	MBR10100CD
Repetitive peak reverse voltage	V _{RRM}	V	100
Average Rectified Output Current @60Hz -sine wave, T _c =130°C	I _O	A	10
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave, 1 cycle, T _a =25°C	I _{FSM}	A	120
Current Squared Time @1ms≤t≤8.3ms T _J =25°C	I ² t	A ² s	60
Storage Temperature	T _{stg}	°C	-55 ~ +175
Junction Temperature	T _J	°C	-55 ~ +175

■Electrical Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS		Typ	Max
Instantaneous forward voltage per diode	V _F	V	I _F =5A	T _J =25°C	0.78	0.8
				T _J =125°C	0.65	0.7
Typical junction capacitance per diode	C _J	pF	V _R =4V, f=1 MHz		160	-
Instantaneous reverse current per diode	I _R	uA	V _R =100V	T _J =25°C	-	10
				T _J =125°C	-	500
Reverse Recovery Time	T _{RR}	ns	I _F =0.5A, I _R =1A, I _{RR} =0.25A, T _J =25°C		11	-

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER		SYMBOL	UNIT	MBR10100CDQ
Typical thermal resistance per diode	Between junction and case	R _{θJ-C}	°C/W	5



■ Characteristics (Typical)

Fig.1: Forward Current Derating Curve

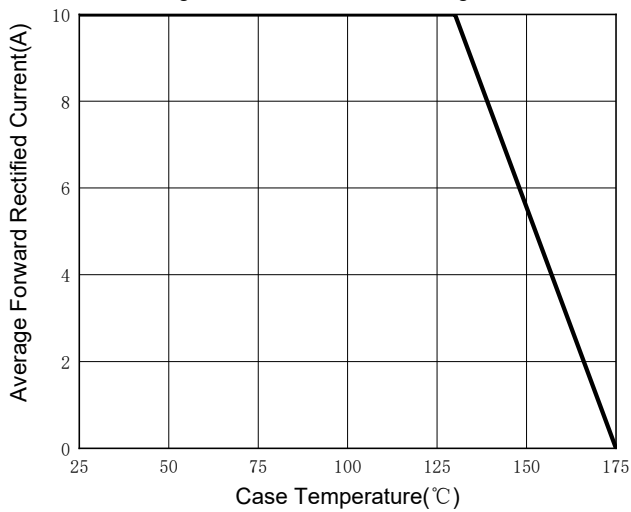


Fig.2: Forward Surge Current Capability (Per Diode)

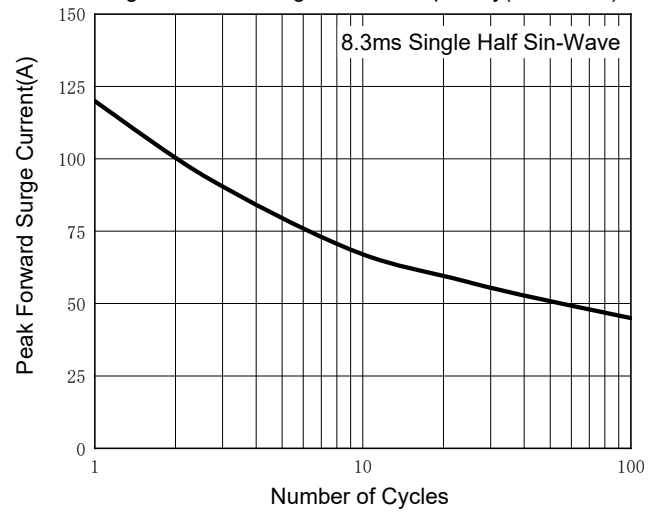


Fig.3: Typical Instantaneous Forward Characteristics (Per Diode)

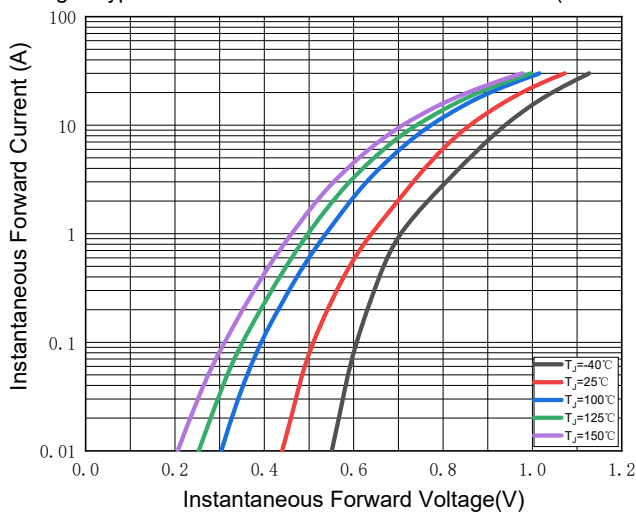


Fig.4: Typical Reverse Leakage Characteristics (Per Diode)

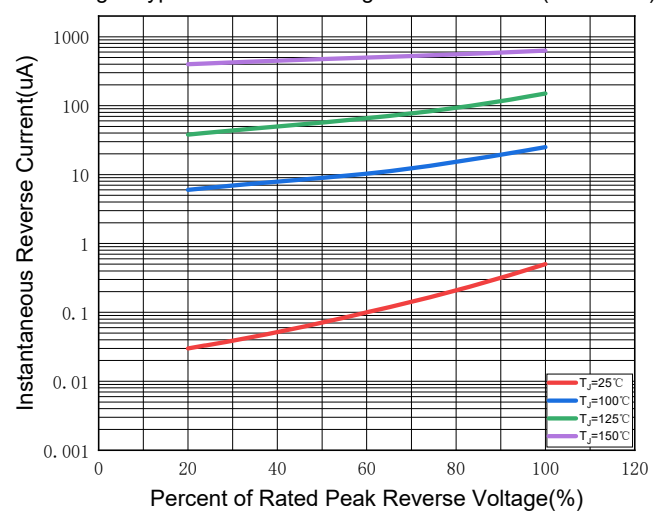
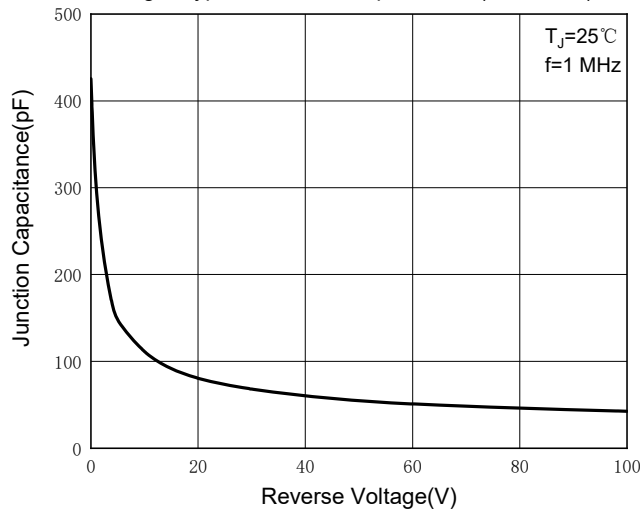


Fig.5: Typical Junction Capacitance (Per Diode)



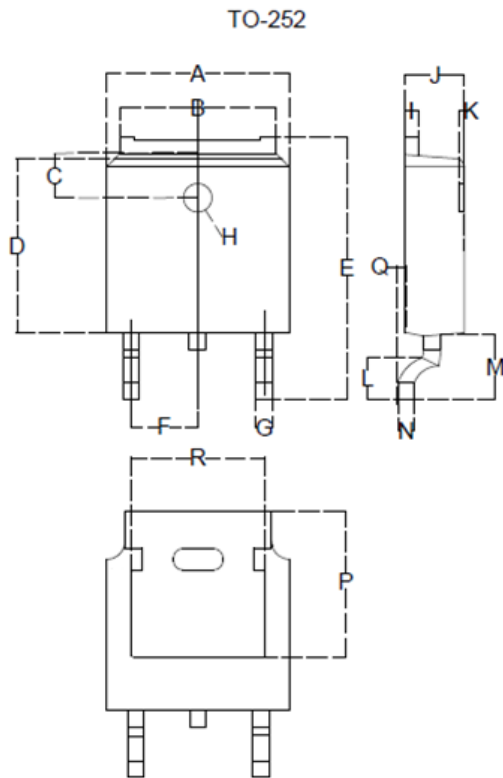


MBR10100CDQ

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR10100CDQ	Approximate 0.32	2500	2500	25000	Reel

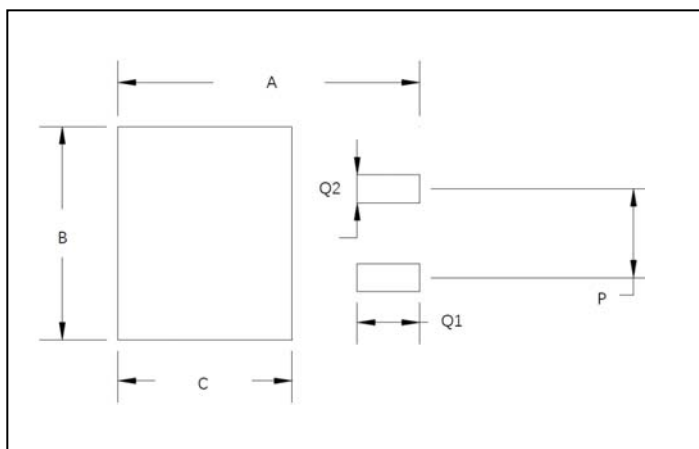
■Outline Dimensions



Dimensions in millimeters

TO-252		
Dim	Min	Max
A	6.500	6.700
B	5.100	5.460
C	1.400	1.800
D	6.000	6.200
E	10.000	10.400
F	2.166	2.366
G	0.660	0.860
H	Φ 1.050	Φ 1.350
I	0.460	0.580
J	2.200	2.400
K	0	0.300
L	0.890	2.290
M	2.730	3.080
N	0.430	0.580
P	5.15	5.45
Q	0	0.2
R	4.500	5.100

■Suggested Pad Layout



Dim	Millimeters
A	10.70
B	5.70
C	6.23
P	4.532
Q1	2.25
Q2	1.21



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